

Claim Amendments

Please amend the claims as follows.

Claims 1-16 (canceled)

17. (currently amended) A surface acoustic wave (SAW) device sealed at the wafer level, the device comprising:
 - an active area to be protected;
 - an electrical contact area; and
 - a lithographically-formed structure hermetically sealing at least the active area and leaving at least a portion of the electrical contact area exposed, wherein the lithographically-formed structure comprises a seal coating deposited over a sacrificial material, said sacrificial material being subsequently removed by etching.
18. (original) The device of claim 17, wherein the lithographically-formed structure comprises a glassy material.
19. (original) The device of claim 17, wherein the SAW device is fabricated on a substrate from a group of substrates consisting of lithium tantalate, lithium niobate, and quartz.
20. (currently amended) A lithographically-fabricated surface acoustic wave (SAW) device, the SAW device comprising:
 - means for carrying a surface acoustic wave; and
 - a wafer-level means for hermetically sealing the means for carrying the surface acoustic wave,wherein said wafer-level means for sealing comprises a seal coating deposited over a sacrificial material, said sacrificial material being subsequently removed by etching.

21. (previously presented) The SAW device of claim 20, wherein the means for carrying the surface acoustic wave comprises a transducer structure.
22. (previously presented) The SAW device of claim 21, wherein the transducer structure comprises aluminum pattered into interdigitated electrode fingers.
23. (previously presented) The SAW device of claim 20, wherein the wafer-level means for sealing comprises a lithographically-formed structure sealing at least the means for carrying.
24. (previously presented) The SAW device of claim 23, further comprising electrical contact areas coupled to the means for carrying, and wherein the wafer-level means for sealing leaves exposed at least a portion of the electrical contact areas.
25. (previously presented) The device of claim 17, wherein the lithographically-formed structure comprises a material of a thickness so as to be impermeable to undesired contaminants.
26. (previously presented) The device of claim 17, wherein the lithographically-formed structure comprises silicon dioxide.
27. (previously presented) The device of claim 17, wherein the lithographically-formed structure comprises silicon nitride.
28. (previously presented) The device of claim 17, wherein the lithographically-formed structure comprises a metal.
29. (previously presented) The device of claim 18, wherein the glassy material comprises a spin-on-glass.

30. (previously presented) The device of claim 18, wherein the glassy material comprises a sputtered glass.
31. (previously presented) The device of claim 17, wherein the SAW device is fabricated on a lithium tantalate substrate.
32. (previously presented) The device of claim 17, wherein the SAW device is fabricated on a lithium niobate substrate.
33. (previously presented) The device of claim 17, wherein the SAW device is fabricated on a quartz substrate.